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Interaction Correction to the Longitudinal Conductivity and Hall Resistivity in High Quality Two-Dimensional GaAs Electron and Hole Systems

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We present a systematic study of the corrections to both the longitudinal conductivity and Hall resistivity due to electron-electron interactions in high quality GaAs systems using the recent theory of Zala *et al.* [Phys. Rev. B **64**, 214204 (2001)]. We demonstrate that the interaction corrections to the longitudinal conductivity and Hall resistivity predicted by the theory are consistent with each other. This suggests that the anomalous metallic drop in resistivity at B=0 is due to interaction effects and supports the theory of Zala *et al.*

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Despite much theoretical and experimental work, to date the origin of the anomalous metallic behavior in high quality 2D systems at zero magnetic field B remains a subject of controversy[1]. The earliest results of Finkelstein[2] and Castellani *et al.*[3] suggested that in the presence of weak disorder and strong interactions it is possible to have a metallic ground state (where the conductivity σ_{xx} assumes a finite value at T=0) in 2D, even at B=0. It is well known that in the diffusive limit $k_BT\tau/\hbar \ll 1$, electron-electron interactions give rise to a logarithmic correction to the conductivity.[4] In the opposite ballistic limit $k_BT\tau/\hbar \gg 1$, Stern,[5] Gold & Dolgopolov,[6] and Das Sarma & Hwang[7] have also shown that σ_{xx} can exhibit a metallic-like temperature dependence that is linear in temperature, and due to temperature-dependent screening of impurity and interface roughness scattering. While these previous theories were formulated in opposite limits of $k_BT\tau/\hbar$, most existing experimental data displaying B=0 metallic behavior falls in the intermediate region between these limits.

Recently, quantum conductivity corrections have received renewed interest following the development of a theory by Zala *et al.*[8] that is valid for the entire range of $k_BT\tau/\hbar$. This theory shows that the previous results in the two opposite limits are due to the same physical process – elastic scattering of electrons by the self-consistent potential created by all the other electrons (i.e., scattering from the screened impurity potential). As the temperature is reduced, Ref. 8 predicts a correction to the conductivity that is either localizing or delocalizing depending on the value of the Fermi liquid parameter F_0^σ. The parameter F_0^σ is a measure of the interaction strength in the triplet channel and is related to the spin susceptibility $\chi \propto 1/(1+F_0^\sigma)$[8]. Several recent experimental studies[9,10,11,12] following Ref. 8 have shown that the B=0 metallic behavior in a variety of material systems is consistent with the theory of Zala *et al.*

In addition to producing a correction to the longitudinal conductivity σ_{xx}, interaction effects also lead to a correction to the Hall resistivity ρ_{xy}.[4,13] Whilst many of these authors have examined the σ_{xx} interaction correction, both at B=0 and in parallel magnetic fields,[9,10,11,12,14] studies of the ρ_{xy} correction are less common.[11,15] In particular there has been no experimental confirmation that the observed correction to ρ_{xy} is consistent with the correction to σ_{xx} or with the theoretical predictions of Ref. 13. Since the magnitude of the corrections to σ_{xx} and ρ_{xy} both depend on F_0^σ, then if the B=0 metallic behavior is due to electron-electron interactions, the two values of F_0^σ extracted separately from measurements of σ_{xx} and ρ_{xy} should be consistent.

In this paper we report a systematic study of the interaction corrections to both the longitudinal conductivity σ_{xx} and Hall resistivity ρ_{xy}, and extracted values for the Fermi liquid parameter, F_0^σ. We show that the values of F_0^σ obtained from these two independent measurements are consistent. Our results support the theory of Zala *et al.* and suggest that the B=0 metallic behavior is due to interaction effects.

The experiments were performed on both n- and p-GaAs samples. The measured mobilities were 8.0 $\times 10^5$ cm^{2}V^{-1}s^{-1} at a carrier density of $n_s = 2.0 \times 10^{10}$ cm^{-2} for the n-GaAs sample, and 2.0 $\times 10^5$ cm^{2}V^{-1}s^{-1} at $n_s = 2.0 \times 10^{11}$ cm^{-2} for the p-GaAs sample. The T-dependence of σ_{xx} shows a transition from insulating to metallic behavior at $n_s = 5.17 \times 10^9$ cm^{-2} (n-GaAs) and 4.50 $\times 10^{10}$ cm^{-2} (p-GaAs). Firstly, we will outline the procedures used to extract the interaction correction and F_0^σ from the experimental measurements of σ_{xx} and ρ_{xy} for the n-GaAs sample. After extracting the interaction correction and F_0^σ for the p-GaAs data, we will present a comparative analysis of F_0^σ for the two samples, and discuss the ramifications of our measurements with respect to the theory of Ref. 8.

We begin by discussing the interaction correction to σ_{xx} and ρ_{xy} in n-GaAs because it is close to the ideal system considered in Ref. 8 – electrons in n-GaAs have spin 1/2, no valley degeneracy, and well defined effective mass $m^* = 0.067 m_e$. Furthermore additional corrections from phonon scattering and weak localization are negligible for the range of experimental parameters that we have explored.

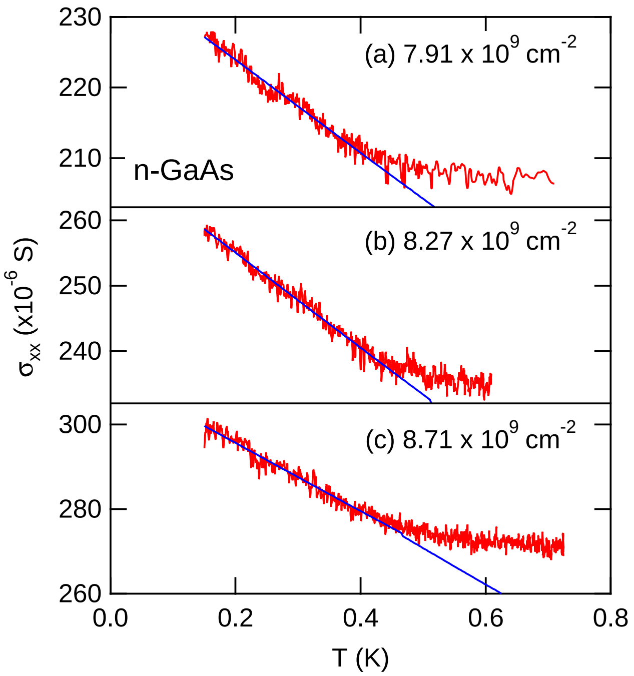

FIG. 1: (a-c) Longitudinal conductivity σ_{xx} vs temperature T from the n-GaAs sample at the indicated carrier densities. The solid lines are fits of Eqn. 1 to the data.

Commencing with the longitudinal conductivity correction, the temperature dependence of σ_{xx} at B=0 can be written as:

$$\sigma_{xx}(T) = \sigma_D + \delta\sigma_S(T) + \delta\sigma_T(T) \qquad (1)$$

where σ_D is the Drude conductivity. The terms $\delta\sigma_S(T)$ and $\delta\sigma_T(T)$ are the singlet and triplet channel interaction corrections given by Zala *et al.* as[8]:

$$\begin{aligned} \delta\sigma_S &= \frac{e^2}{\pi h}\left[f(k_B T\tau)\frac{k_B T\tau}{h} - \ln\left(\frac{E_F}{T}\right)\right] \qquad (2) \\ \delta\sigma_T &= \frac{e^2}{\pi h}\left[g(k_B T\tau; F_0^\sigma)\frac{k_B T\tau}{h} - h(F_0^\sigma)\ln\left(\frac{E_F}{T}\right)\right] \end{aligned}$$

where $f(x)$, $g(x; F_0^\sigma)$ and $h(x)$ are detailed in Ref. 8. The procedure for extracting F_0^σ involves fitting Eqn. 1 to the graph of σ_{xx} vs. T in the degenerate limit $T \ll T_F$. The Fermi energy E_F and momentum scattering time τ are given by $E_F = \pi\hbar^2 n_s/m^*$ and $\sigma_D = n_s e^2\tau/m^*$ respectively using measured values of n_s and σ_D. This leaves F_0^σ as the only fitting parameter in Eqn. 1.

Figure 1 (a-c) shows σ_{xx} vs. T for the n-GaAs sample at three values of n_s. At all carrier densities, σ_{xx} decreases linearly with increasing T up to ∼0.5 K, above which σ_{xx} levels off, and after reaching a minimum value (not shown), increases again for higher T. This deviation from the low T linear behavior has been observed previously and is due to the 2D system becoming non-degenerate.[7,17] Fits of Eqn. 1 to the experimental data are shown as solid lines in Fig. 1. The fitting was limited to $T/T_F \leq 0.15$ where non-degenerate behavior is not observed. The resulting values of F_0^σ extracted from the fits, both with and without accounting for phonon scattering, are found to be very similar (within 3%)[16] and lie in the range $-0.4 < F_0^\sigma < -0.36$; we will return to discuss these extracted F_0^σ values in more detail later.

We now turn to the correction to ρ_{xy}, which despite involving a longer procedure to extract, is significantly simpler than the correction to σ_{xx}. This is because effects such as weak localization and phonon scattering have no impact on the T-dependence of ρ_{xy} and can be safely ignored. The Hall resistivity is composed of three terms

$$\rho_{xy}(T) = \rho_H^D + \delta\rho_{xy}^\rho(T) + \delta\rho_{xy}^\sigma(T) \qquad (3)$$

where $\rho_H^D = -B/n_s e$ is the classical Hall resistivity, $\delta\rho_{xy}^\rho$ and $\delta\rho_{xy}^\sigma$ are the singlet and triplet interaction correction terms given by:[13]

$$\begin{aligned} \frac{\delta\rho_{xy}^\rho}{\rho_H^D} &= \frac{e^2}{\pi^2\hbar\sigma_D}\left[\frac{11\pi}{192}\frac{\hbar}{k_B T\tau} + \ln\left(1 + \frac{11\pi}{192}\frac{\hbar}{k_B T\tau}\right)\right] (4) \\ \frac{\delta\rho_{xy}^\sigma}{\rho_H^D} &= \frac{3e^2}{\pi^2\hbar\sigma_D} f(F_0^\sigma)\ln\left(1 + \frac{11\pi}{192}\frac{\hbar}{k_B T\tau}\right) \end{aligned}$$

where $f(x)$ is detailed in Ref. 13.

The procedure for extracting F_0^σ involves three steps: (i) The Hall slopes $d\rho_{xy}(T)/dB$ are obtained from the $\rho_{xy}(T)$ traces as the gradient of linear fits over the range –20 mT $< B <$ 20 mT. (ii) In the high temperature limit both $\delta\rho_{xy}^\rho$ and $\delta\rho_{xy}^\sigma \to 0$ so that $\rho_{xy}(T) = \rho_H^D$, allowing ρ_H^D to be determined. Here, we take ρ_H^D as ρ_{xy} at 600 mK, the highest measurement temperature. (iii) F_0^σ is then obtained by fitting Eqn. 3 to a plot of $d\rho_{xy}(T)/dB$ vs. $k_B T\tau/\hbar$, with τ determined as specified earlier and F_0^σ as the only fit parameter.

Figure 2 (a-c) shows plots of $\rho_{xy}(T)$ vs. B at several temperatures in the range 150 mK $< T <$ 600 mK, for n_s values corresponding to those in Fig. 1. In each case the slope of $\rho_{xy}(T)$ vs. B decreases by $\sim$ 1.5% as the temperature is raised from 150 mK to 600 mK. This temperature-induced slope change is more clearly shown in Fig. 2 (c) (inset) where we plot the difference between the straight line fits to the Hall resistivity at T and 600 mK, $\Delta\rho_{xy}(T) = \rho_{xy}(T) - \rho_{xy}(600mK)$ vs. B as a function of T. We have confirmed that this slope change is not due to variations in n_s by tracking the Shubnikov-de Haas (SdH) oscillations as a function of T – we find that the SdH minima occur at constant B to within 0.1 % as T is varied.

Figure 2 (d-f) shows the extracted Hall slope $d\rho_{xy}(T)/dB$ as a function of $k_BT\tau/\hbar$. Since it is difficult to reliably cool 2D systems to temperatures below 100 mK[19], we only present experimental data where we have confirmed that the electron temperature matches the lattice temperature using Arrhenius plots of the SdH minima.

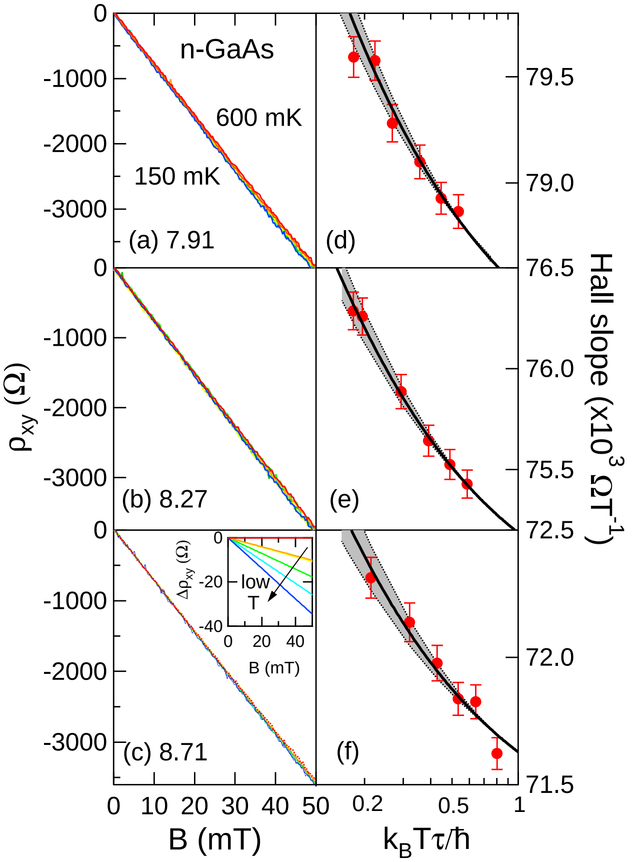

FIG. 2: Left panel (a-c) shows the Hall resistivity ρ_{xy} at the indicated carrier densities (in $\times 10^9$ cm^{-2}) for the n-GaAs sample at temperatures ranging from 150 mK to 600 mK. Inset shows the difference between the straight line fits at T and 600 mK, $\Delta\rho_{xy} = \rho_{xy}(T) - \rho_{xy}(600mK)$, the arrow indicates decreasing T. Values of the Hall slope are presented in the right panel (d-f) along with the fit. The shaded region indicates the error in the fitting.

Fits of Eqn. 3 to the $d\rho_{xy}(T)/dB$ vs. $k_BT\tau/\hbar$ data are shown as solid lines in Fig. 2 (d-f), the shaded region indicates one standard deviation of error for the fit. Before we discuss the values of F_0^σ extracted from the n-GaAs data, we will first repeat this analysis to extract interaction corrections for the p-GaAs sample, which also shows metallic behavior at B=0. Commencing with obtaining F_0^σ from the σ_{xx} correction, weak localization effects are not negligible and hence we need to subtract the weak localization correction from the B=0 σ_{xx} data before fitting with Eqn. 1 to extract values for F_0^σ. The weak localization correction to the conductivity was obtained by fitting the low field magnetoconductivity using the theory of Dmitriev *et al.*,[20] which is valid over a wider range of B than the simpler theory of Hikami *et al.*[21,22]

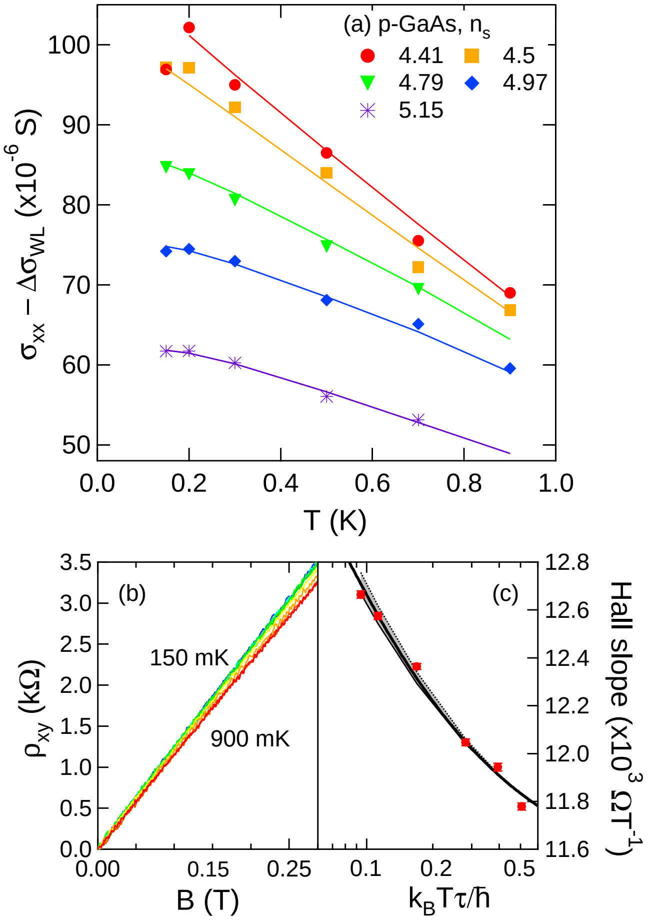

FIG. 3: (a) Longitudinal conductivity σ_{xx} of the p-GaAs sample after subtracting the weak localization correction $\Delta\sigma_{WL}$ at the indicated carrier densities (in $\times 10^{10}$ cm^{-2}). (b) The Hall resistivity ρ_{xy} at $n_s = 4.97 \times 10^{10}$ cm^{-2} for different temperatures from 150 mK to 900 mK, and (c) the corresponding Hall slope along with the fit to Eqn. 3. The shaded region indicates the error in the fitting.

The resulting values of $\sigma_{xx} - \Delta\sigma_{WL}$ for several different carrier densities are presented in Fig. 3(a) along with the fits of Eqn. 1. At each n_s, the theory fits the experimental data well. The phonon contribution is again small compared to $\delta\sigma_{xx}(T)$ and fitting with or without the phonon term gives similar values of F_0^σ (within 5%);[16] this will be discussed later.

To obtain an independent measurement of F_0^σ in the p-GaAs sample, we again study the T-dependent corrections to ρ_{xy}. Fig. 3(b) presents a typical ρ_{xy} trace at several different temperatures, showing a decrease in the slope of ρ_{xy} as T is increased from 150 mK to 900 mK. Again we have confirmed that changes in the Hall slope are not due to changes in carrier density.[15,18] The Hall slope $d\rho_{xy}(T)/dB$ vs. $k_BT\tau/\hbar$ is presented in Fig. 3(c) along with a fit of Eqn. 3, which describes the experimental data reasonably well. The fit quality for the p-GaAs data is poorer than that of the n-GaAs and is likely due to the fact that p-GaAs is a more complex experimental system (e.g. m^* not well known, holes are spin 3/2 particles).

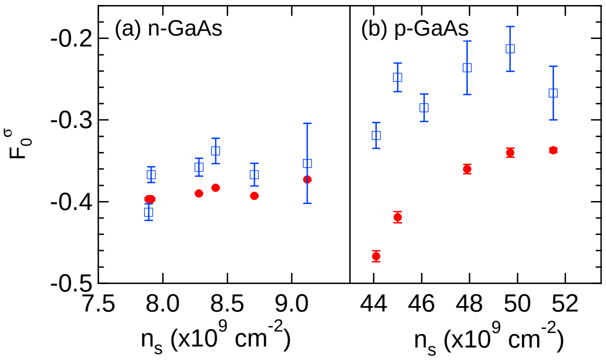

FIG. 4: Values of the Fermi liquid parameter F_0^σ extracted from $\sigma_{xx}(T)$ at B=0 (solid) and $\rho_{xy}(T)$ (open) as a function of n_s for the (a) n-GaAs and (b) p-GaAs samples.

Fig. 4 contains the key result of our study. Firstly in Fig. 4 (a) we plot the values of F_0^σ extracted from σ_{xx} (solid circles) and ρ_{xy} (open squares) as a function of n_s for the n-GaAs sample. The error bars correspond to the fit errors discussed earlier (for the σ_{xx} data in Fig. 4 (a), these are too small to show). As the carrier density is increased, F_0^σ increases in agreement with both theoretical expectations[8] and previous studies.[9,10,11,14] Most significantly at all carrier densities, the F_0^σ values extracted using the two different methods agree to within 9%. The excellent agreement can only occur if the corrections to σ_{xx} and ρ_{xy} originate from the same mechanism, thereby supporting the theory of Zala *et al.* that these corrections both derive from electron-electron screening of scattering processes.

Secondly, we plot the data for F_0^σ extracted from σ_{xx} (solid circles) and ρ_{xy} (open squares) as a function of n_s in Fig. 4 (b) for the p-GaAs sample. A number of features stand out in this data. For both methods of extracting F_0^σ we see qualitatively similar behavior – in general F_0^σ decreases with decreasing n_s – to that observed in the n-GaAs data. However, in contrast to the n-GaAs data, there is a marked quantitative discrepancy between the F_0^σ values extracted from the two methods, with the values differing by 30 %. This discrepancy suggests that additional corrections may be involved in the p-GaAs data, which is not entirely unexpected. Although the interaction effects are easier to measure due to the significantly larger r_s in p-GaAs, the holes are spin 3/2 particles and the effective mass is not well known (we have taken it as $m^* = 0.3m_e$ here), making comparisons between experimental data and the theory of Zala *et al.*[8] a more complicated prospect. However, despite the quantitative discrepancy, the qualitative trends in the p-GaAs data still support Ref. 8 and suggest that the anomalous B=0 metallic behavior is due to electron-electron or hole-hole interactions, in agreement with previous studies in p-GaAs,[9,12] n-Si,[10] p-SiGe,[11] and n-GaAs.[23]

In summary, we present a study of the interaction correction in both 2D GaAs electron and hole systems using the theory of Zala *et al.*[8,13] We find that independent measurements of the interaction correction from the B=0 T-dependence of σ_{xx} and the low-B ρ_{xy} are in excellent agreement for the n-GaAs system, and are quantitatively consistent to within 30%, and in good qualitative agreement in p-GaAs. This supports the theory of Zala *et al.*[8] in explaining the anomalous B=0 metallic behavior as due to electron-electron interactions screening the impurity potential.

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